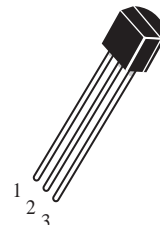


## Driver NPN Transistors

**(Pb)** Lead(Pb)-Free

**TO-92**

1. EMITTER  
2. BASE  
3. COLLECTOR



### ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Rating	Symbol	MPSA05	MPSA06	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	60	80	V <sub>dc</sub>
Collector-Base Voltage	V <sub>CBO</sub>	60	80	V <sub>dc</sub>
Emitter-Base Voltage	V <sub>EBO</sub>	4.0		V <sub>dc</sub>
Collector Current	I <sub>C</sub>	500		mA <sub>dc</sub>
Total Device Dissipation T <sub>A</sub> =25°C	P <sub>D</sub>	0.625		W
Junction Temperature	T <sub>j</sub>	150		°C
Storage, Temperature	T <sub>stg</sub>	-55 to +150		°C

### ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , I <sub>B</sub> =0) MPSA05 MPSA06	V <sub>(BR)CEO</sub>	60 80	-	V <sub>dc</sub>
Collector-Base Breakdown Voltage (I <sub>C</sub> = 100 uA <sub>dc</sub> , I <sub>E</sub> =0) MPSA05 MPSA06	V <sub>(BR)CBO</sub>	60 80	-	V <sub>dc</sub>
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 100 uA <sub>dc</sub> , I <sub>C</sub> =0)	V <sub>(BR)EBO</sub>	4.0	-	V <sub>dc</sub>
Collector Cutoff Current (V <sub>CE</sub> = 50 V <sub>dc</sub> , I <sub>B</sub> =0) MPSA05 (V <sub>CE</sub> = 60 V <sub>dc</sub> , I <sub>B</sub> =0) MPSA06	I <sub>CEO</sub>	-	0.1	uA <sub>dc</sub>
Collector Cutoff Current (V <sub>CE</sub> = 60 V <sub>dc</sub> , I <sub>B</sub> =0) MPSA05 (V <sub>CE</sub> = 80 V <sub>dc</sub> , I <sub>B</sub> =0) MPSA06	I <sub>CBO</sub>	-	0.1	uA <sub>dc</sub>
Emitter Cutoff Current (V <sub>EB</sub> = 3.0V <sub>dc</sub> , I <sub>C</sub> =0)	I <sub>EBO</sub>	-	0.1	uA <sub>dc</sub>

**MPSA05**  
**MPSA06**

**WEITRON**

**ELECTRICAL CHARACTERISTICS** ( $T_A=25^\circ\text{C}$  unless otherwise noted) (Continued)

Characteristics	Symbol	Min	TYP	Max	Unit
-----------------	--------	-----	-----	-----	------

**ON CHARACTERISTICS**

DC Current Gain ( $I_C=100\text{ mAdc}, V_{CE}=1.0\text{ Vdc}$ )	$h_{FE(1)}$	100	-	-	-
Collector-Emitter Saturation Voltage ( $I_C=100\text{ mAdc}, I_B=10\text{ mAdc}$ )	$V_{CE(sat)}$	-	-	0.25	Vdc
Base-Emitter Saturation Voltage ( $I_C=100\text{ mAdc}, I_B=10\text{ mAdc}$ )	$V_{BE(sat)}$	-	-	1.2	Vdc
Current-Gain-Bandwidth Product ( $I_C=10\text{ mAdc}, V_{CE}=2.0\text{ Vdc}, f=100\text{ MHz}$ )	$f_T$	100	-	-	MHz

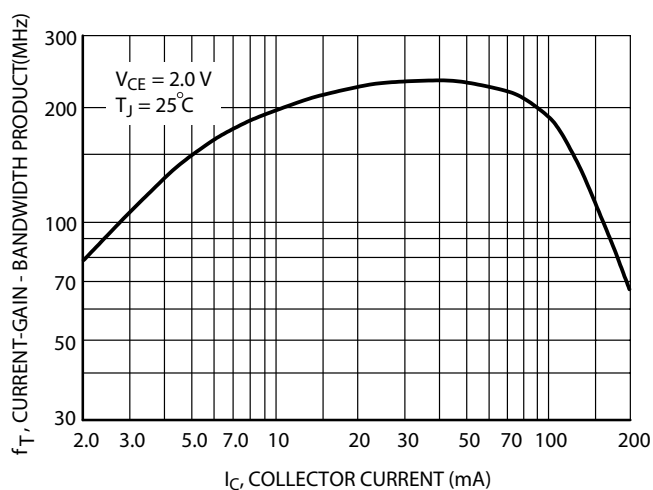


FIG1. Current-Gain Bandwidth Product

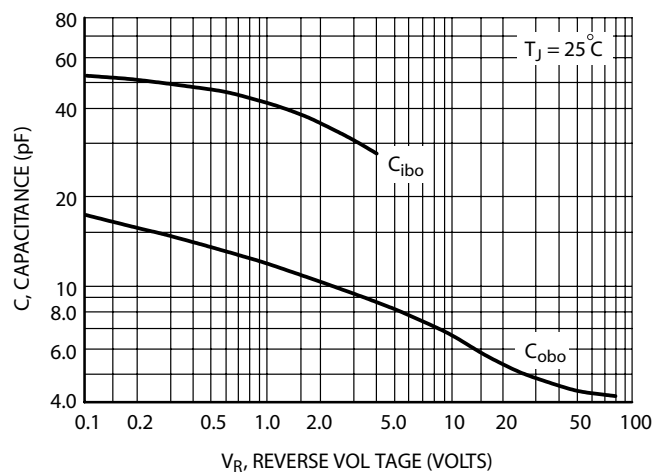


FIG2. Capacitance

**MPSA05  
MPSA06**

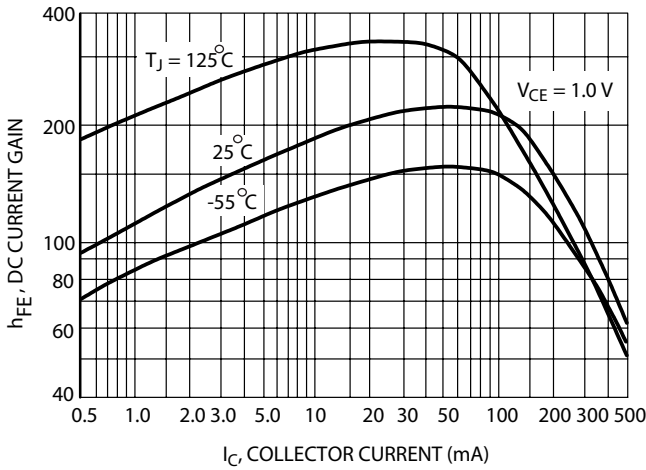


FIG3. DC Current Gain

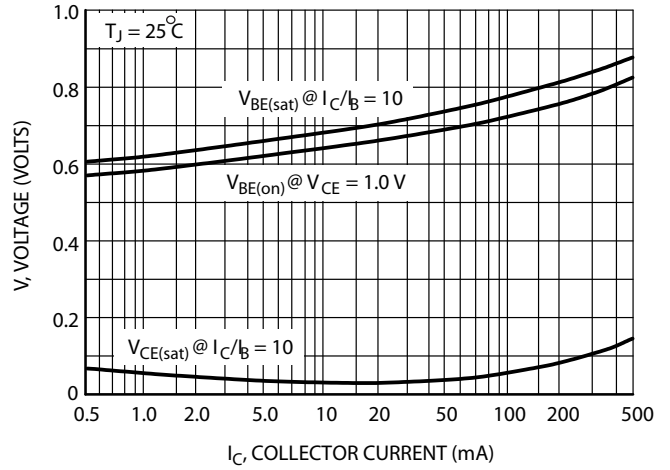


FIG4. "ON" Voltages

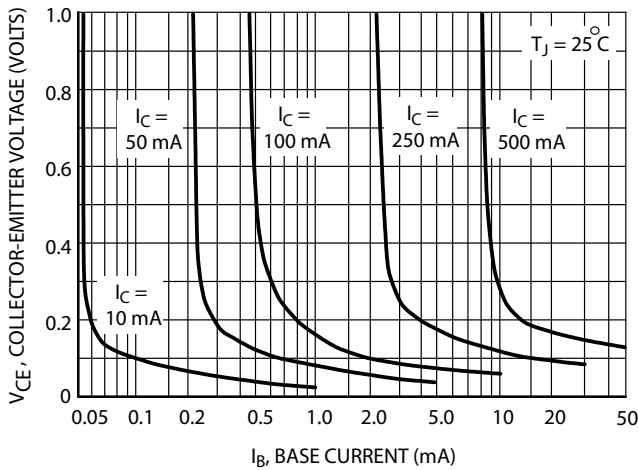


FIG5. Collector Saturation Region

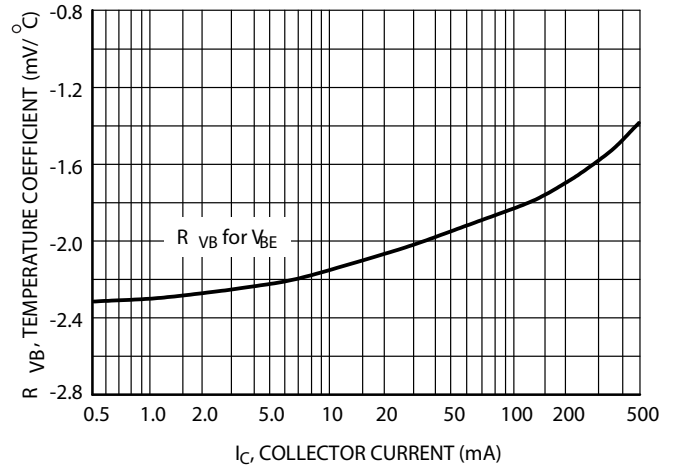


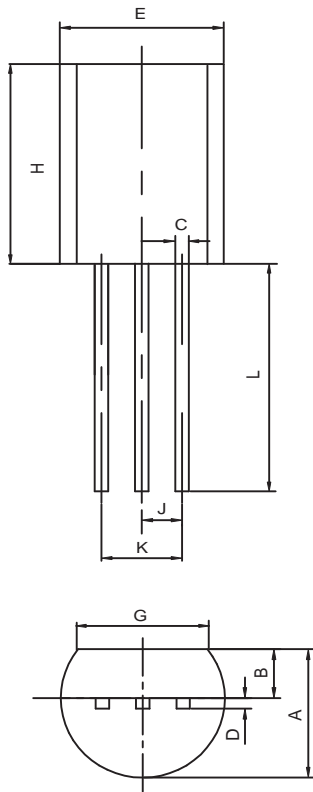
FIG6. Base-Emitter Temperature Coefficient

**MPSA05**  
**MPSA05**

**WEITRON**

## TO-92 Outline Dimensions

unit:mm



<b>TO-92</b>		
<b>Dim</b>	<b>Min</b>	<b>Max</b>
<b>A</b>	3.30	3.70
<b>B</b>	1.10	1.40
<b>C</b>	0.38	0.55
<b>D</b>	0.36	0.51
<b>E</b>	4.40	4.70
<b>G</b>	3.43	-
<b>H</b>	4.30	4.70
<b>J</b>	1.270TYP	
<b>K</b>	2.44	2.64
<b>L</b>	14.10	14.50